Ivan G Ivanov

List of Publications by Year
in descending order

211 papers	4,253 citations	126907 33 h-index	161849 54 g-index
214 all docs	214 docs citations	214 times ranked	3955 citing authors

#	Article	IF	Citations
1	Fluorescence spectrum and charge state control of divacancy qubits via illumination at elevated temperatures in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>4</mml:mn><mml:mi>H</mml:mi></mml:mrow></mml silicon carbide. Physical Review B, 2022, 105, .	3.2	5
2	Bidirectional Hydrogen Electrocatalysis on Epitaxial Graphene. ACS Omega, 2022, 7, 13221-13227.	3.5	4
3	Understanding of the Electrochemical Behavior of Lithium at Bilayer-Patched Epitaxial Graphene/4H-SiC. Nanomaterials, 2022, 12, 2229.	4.1	3
4	Modified divacancies in 4H-SiC. Journal of Applied Physics, 2022, 132, .	2.5	3
5	MOCVD of AlN on epitaxial graphene at extreme temperatures. CrystEngComm, 2021, 23, 385-390.	2.6	46
6	Resolving mobility anisotropy in quasi-free-standing epitaxial graphene by terahertz optical Hall effect. Carbon, 2021, 172, 248-259.	10.3	4
7	Critical View on Buffer Layer Formation and Monolayer Graphene Properties in High-Temperature Sublimation. Applied Sciences (Switzerland), 2021, 11, 1891.	2.5	3
8	Exploring the Interface Landscape of Noble Metals on Epitaxial Graphene. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000673.	1.8	9
9	Charge state control of the silicon vacancy and divacancy in silicon carbide. Journal of Applied Physics, 2021, 129, .	2.5	16
10	Deep levels related to the carbon antisiteâ€"vacancy pair in 4H-SiC. Journal of Applied Physics, 2021, 130, .	2.5	5
11	Study of Cucurbit[7]uril nanocoating on epitaxial graphene to design a versatile sensing platform. Applied Surface Science, 2021, 563, 150096.	6.1	2
12	Clustering and Morphology Evolution of Gold on Nanostructured Surfaces of Silicon Carbide: Implications for Catalysis and Sensing. ACS Applied Nano Materials, 2021, 4, 1282-1293.	5.0	10
13	Silver nanoparticle array on weakly interacting epitaxial graphene substrate as catalyst for hydrogen evolution reaction under neutral conditions. Applied Physics Letters, 2021, 119, 153902.	3.3	2
14	Manipulation of epitaxial graphene towards novel properties and applications. Materials Today: Proceedings, 2020, 20, 37-45.	1.8	2
15	Probing the uniformity of silver-doped epitaxial graphene by micro-Raman mapping. Physica B: Condensed Matter, 2020, 580, 411751.	2.7	10
16	Surface functionalization of epitaxial graphene using ion implantation for sensing and optical applications. Carbon, 2020, 157, 169-184.	10.3	15
17	Interplay between thin silver films and epitaxial graphene. Surface and Coatings Technology, 2020, 381, 125200.	4.8	6
18	Nanoscale phenomena ruling deposition and intercalation of AlN at the graphene/SiC interface. Nanoscale, 2020, 12, 19470-19476.	5.6	54

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19	Direct epitaxial nanometer-thin InN of high structural quality on 4Hâ€“SiC by atomic layer deposition. Applied Physics Letters, 2020, 117, .	3.3	11
20	Reactive sputtering of CSx thin solid films using CS2 as precursor. Vacuum, 2020, 182, 109775.	3.5	13
21	Developing silicon carbide for quantum spintronics. Applied Physics Letters, 2020, 116, .	3.3	101
22	Epitaxial Graphene Growth on the Stepâ€Structured Surface of Offâ€Axis Câ€Face 3Câ€SiC(1Â¯1Â¯1Â¯). Physica Status Solidi (B): Basic Research, 2020, 257, 1900718.	1.5	1
23	A patterning-free approach for growth of free-standing graphene nanoribbons using step-bunched facets of off-oriented 4H-SiC(0â€‰0â€‰0â€‰1) epilayers. Journal Physics D: Applied Physics, 2020, 53, 115102.	2.8	2
24	Excitonic emission in heavily Ga-doped zinc oxide films grown on GaN. Journal of Luminescence, 2020, 223, 117265.	3.1	7
25	In Situ Activation of an Indium(III) Triazenide Precursor for Epitaxial Growth of Indium Nitride by Atomic Layer Deposition. Chemistry of Materials, 2020, 32, 4481-4489.	6.7	26
26	Spin-relaxation times exceeding seconds for color centers with strong spinâ€“orbit coupling in SiC. New Journal of Physics, 2020, 22, 103051.	2.9	15
27	Bioelectrocatalysis on Anodized Epitaxial Graphene and Conventional Graphitic Interfaces. ChemElectroChem, 2019, 6, 3791-3796.	3.4	2
28	Electrical Charge State Manipulation of Single Silicon Vacancies in a Silicon Carbide Quantum Optoelectronic Device. Nano Letters, 2019, 19, 7173-7180.	9.1	61
29	The Endocyclic Carbon Substituent of Guanidinate and Amidinate Precursors Controlling Atomic Layer Deposition of InN Films. Journal of Physical Chemistry C, 2019, 123, 25691-25700.	3.1	19
30	A comparative study of high-quality C-face and Si-face 3C-SiC(1â€‰1â€‰1) grown on off-oriented 4H-SiC substrates. Journal Physics D: Applied Physics, 2019, 52, 345103.	2.8	16
31	Energy levels and charge state control of the carbon antisite-vacancy defect in 4H-SiC. Applied Physics Letters, 2019, 114, .	3.3	17
32	Seedâ€Layerâ€Free Atomic Layer Deposition of Highly Uniform Al₂O₃ Thin Films onto Monolayer Epitaxial Graphene on Silicon Carbide. Advanced Materials Interfaces, 2019, 6, 1900097.	3.7	24
33	Effect of epitaxial graphene morphology on adsorption of ambient species. Applied Surface Science, 2019, 486, 239-248.	6.1	17
34	High-fidelity spin and optical control of single silicon-vacancy centres in silicon carbide. Nature Communications, 2019, 10, 1954.	12.8	167
35	Anodization study of epitaxial graphene: insights on the oxygen evolution reaction of graphitic materials. Nanotechnology, 2019, 30, 285701.	2.6	2
36	Atomic layer deposition of InN using trimethylindium and ammonia plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, .	2.1	33

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37	Ligand hyperfine interactions at silicon vacancies in 4H-SiC. Journal of Physics Condensed Matter, 2019, 31, 195501.	1.8	13
38	Probing the uniformity of hydrogen intercalation in quasi-free-standing epitaxial graphene on SiC by micro-Raman mapping and conductive atomic force microscopy. Nanotechnology, 2019, 30, 284003.	2.6	23
39	Real-time sensing of lead with epitaxial graphene-integrated microfluidic devices. Sensors and Actuators B: Chemical, 2019, 288, 425-431.	7.8	34
40	Raman probing of hydrogen-intercalated graphene on Si-face 4H-SiC. Materials Science in Semiconductor Processing, 2019, 96, 145-152.	4.0	16
41	Investigation of LPE grown dilute nitride InGaAs(Sb)N layers for photovoltaic applications. AIP Conference Proceedings, 2019, , .	0.4	1
42	CVD growth and properties of on-axis vanadium doped semi-insulating 4H-SiC epilayers. Journal of Applied Physics, 2019, 125, .	2.5	10
43	First-Principles Study on Photoluminescence Quenching of Divacancy in 4H SiC. Materials Science Forum, 2019, 963, 714-717.	0.3	1
44	Silicon carbonitride thin films deposited by reactive high power impulse magnetron sputtering. Surface and Coatings Technology, 2018, 335, 248-256.	4.8	14
45	Quantum Properties of Dichroic Silicon Vacancies in Silicon Carbide. Physical Review Applied, 2018, 9, .	3.8	90
46	Defects in silicon carbide grown by fluorinated chemical vapor deposition chemistry. Physica B: Condensed Matter, 2018, 535, 44-49.	2.7	3
47	Iron Oxide Nanoparticle Decorated Graphene for Ultra-Sensitive Detection of Volatile Organic Compounds. Proceedings (mdpi), 2018, 2, .	0.2	1
48	Understanding Graphene Response to Neutral and Charged Lead Species: Theory and Experiment. Materials, 2018, 11, 2059.	2.9	11
49	Excitation properties of the divacancy in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>4</mml:mn><mml:mi>H</mml:mi><mml:mrow></mml:mrow> -SiC. Physical Review B, 2018, 98, .	3.2	44
50	Identification and tunable optical coherent control of transition-metal spins in silicon carbide. Npj Quantum Information, 2018, 4, .	6.7	53
51	Lead (Pb) interfacing with epitaxial graphene. Physical Chemistry Chemical Physics, 2018, 20, 17105-17116.	2.8	18
52	Performance tuning of gas sensors based on epitaxial graphene on silicon carbide. Materials and Design, 2018, 153, 153-158.	7.0	25
53	Elimination of step bunching in the growth of large-area monolayer and multilayer graphene on off-axis 3C SiC (111). Carbon, 2018, 140, 533-542.	10.3	14
54	Surface functionalization of epitaxial graphene on SiC by ion irradiation for gas sensing application. Applied Surface Science, 2017, 403, 707-716.	6.1	24

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55	Multi-scale investigation of interface properties, stacking order and decoupling of few layer graphene on C-face 4H-SiC. Carbon, 2017, 116, 722-732.	10.3	23
56	Experimental study of the effect of local atomic ordering on the energy band gap of melt grown InGaAsN alloys. Semiconductor Science and Technology, 2017, 32, 085005.	2.0	13
57	Rolling performance of carbon nitride-coated bearing components in different lubrication regimes. Tribology International, 2017, 114, 141-151.	5.9	22
58	Monitoring of epitaxial graphene anodization. Electrochimica Acta, 2017, 238, 91-98.	5.2	18
59	Calibration on wide-ranging aluminum doping concentrations by photoluminescence in high-quality uncompensated p-type 4H-SiC. Applied Physics Letters, 2017, 111, .	3.3	11
60	In-situ terahertz optical Hall effect measurements of ambient effects on free charge carrier properties of epitaxial graphene. Scientific Reports, 2017, 7, 5151.	3.3	23
61	Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. ECS Journal of Solid State Science and Technology, 2017, 6, P741-P745.	1.8	1
62	(Invited) Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. ECS Transactions, 2017, 80, 107-115.	0.5	1
63	Optical properties of thick GaInAs(Sb)N layers grown by liquid-phase epitaxy. Journal of Physics: Conference Series, 2017, 794, 012013.	0.4	4
64	Growth optimization and applicability of thick on-axis SiC layers using sublimation epitaxy in vacuum. Journal of Crystal Growth, 2016, 448, 51-57.	1.5	4
65	Surface engineering of SiC via sublimation etching. Applied Surface Science, 2016, 390, 816-822.	6.1	10
66	Surface photovoltage and photoluminescence study of thick Ga(In)AsN layers grown by liquid-phase epitaxy. Journal of Physics: Conference Series, 2016, 700, 012028.	0.4	8
67	Trimethylboron as Single-Source Precursor for Boronâ€"Carbon Thin Film Synthesis by Plasma Chemical Vapor Deposition. Journal of Physical Chemistry C, 2016, 120, 21990-21997.	3.1	11
68	Modified Epitaxial Graphene on SiC for Extremely Sensitive and Selective Gas Sensors. Materials Science Forum, 2016, 858, 1145-1148.	0.3	8
69	Light emission enhancement from ZnO nanostructured films grown on Gr/SiC substrates. Carbon, 2016, 99, 295-301.	10.3	6
70	A comparative study of direct current magnetron sputtering and high power impulse magnetron sputtering processes for CNx thin film growth with different inert gases. Diamond and Related Materials, 2016, 64, 13-26.	3.9	20
71	Chloride-based SiC growth on a-axis 4Hâ€"SiC substrates. Physica B: Condensed Matter, 2016, 480, 23-25.	2.7	3
72	Optical properties and Zeeman spectroscopy of niobium in silicon carbide. Physical Review B, 2015, 92, .	3.2	6

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73	Wafer-scale epitaxial graphene on SiC for sensing applications. Proceedings of SPIE, 2015, , .	0.8	2
74	Brominated Chemistry for Chemical Vapor Deposition of Electronic Grade SiC. Chemistry of Materials, 2015, 27, 793-801.	6.7	9
75	Assessment of H-intercalated graphene for microwave FETs through material characterization and electron transport studies. Carbon, 2015, 81, 96-104.	10.3	7
76	Single Domain 3C-SiC Growth on Off-Oriented 4H-SiC Substrates. Crystal Growth and Design, 2015, 15, 2940-2947.	3.0	38
77	Graphene self-switching diodes as zero-bias microwave detectors. Applied Physics Letters, 2015, 106, .	3.3	33
78	Low-temperature growth of low friction wear-resistant amorphous carbon nitride thin films by mid-frequency, high power impulse, and direct current magnetron sputtering. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	2.1	17
79	Quasi-free-standing monolayer and bilayer graphene growth on homoepitaxial on-axis 4H-SiC(0 0 0 1) layers. Carbon, 2015, 82, 12-23.	10.3	16
80	Hydrogen at zinc vacancy of ZnO: An EPR and ESEEM study. , 2014, , .		4
81	Stable and metastable Si negative-U centers in AlGaN and AlN. Applied Physics Letters, 2014, 105, .	3.3	47
82	Lateral Enlargement Growth Mechanism of 3C-SiC on Off-Oriented 4H-SiC Substrates. Crystal Growth and Design, 2014, 14, 6514-6520.	3.0	46
83	Resonant ionization of shallow donors in electric field. Physica Scripta, 2014, 89, 085802.	2.5	0
84	On the use of methane as a carbon precursor in Chemical Vapor Deposition of silicon carbide. Journal of Crystal Growth, 2014, 390, 24-29.	1.5	18
85	Layer-number determination in graphene on SiC by reflectance mapping. Carbon, 2014, 77, 492-500.	10.3	48
86	Reactive high power impulse magnetron sputtering of CFx thin films in mixed Ar/CF4 and Ar/C4F8 discharges. Thin Solid Films, 2013, 542, 21-30.	1.8	17
87	Process stability and morphology optimization of very thick 4Hâ€"SiC epitaxial layers grown by chloride-based CVD. Journal of Crystal Growth, 2013, 380, 55-60.	1.5	23
88	Negative-U behavior of the Si donor in Al0.77Ga0.23N. Applied Physics Letters, 2013, 103, 042101.	3.3	9
89	Reduction of structural defects in thick 4H-SiC epitaxial layers grown on 4Â° off-axis substrates. Journal of Applied Physics, 2013, 113, .	2.5	26
90	Defects in N, O and N, Zn implanted ZnO bulk crystals. Journal of Applied Physics, 2013, 113, .	2.5	34

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91	Magnetic resonance identification of hydrogen at a zinc vacancy in ZnO. Journal of Physics Condensed Matter, 2013, 25, 335804.	1.8	13
92	Electronic Configuration of Tungsten in 4H-, 6H-, and 15R-SiC. Materials Science Forum, 2012, 717-720, 211-216.	0.3	0
93	Considerably long carrier lifetimes in high-quality 3C-SiC(111). Applied Physics Letters, 2012, 100, .	3.3	29
94	Optical identification and electronic configuration of tungsten in 4H- and 6H-SiC. Physica B: Condensed Matter, 2012, 407, 1462-1466.	2.7	14
95	CFx thin solid films deposited by high power impulse magnetron sputtering: Synthesis and characterization. Surface and Coatings Technology, 2011, 206, 646-653.	4.8	43
96	Splitting of type-I (N-B, P-Al) and type-II (N-Al, N-Ga) donor-acceptor pair spectra in 3C-SiC. Physical Review B, 2011, 83, .	3.2	6
97	A SIMS study on Mg diffusion in Zn0.94Mg0.06O/ZnO heterostructures grown by metal organic chemical vapor deposition. Applied Surface Science, 2011, 257, 8629-8633.	6.1	13
98	Ionization energy of the phosphorus donor in 3Câ€"SiC from the donor-acceptor pair emission. Journal of Applied Physics, 2010, 108, .	2.5	7
99	EPR and ENDOR Studies of Shallow Donors in SiC. Applied Magnetic Resonance, 2010, 39, 49-85.	1.2	14
100	AlGaN Multiple Quantum Wells and AlN Grown in a Hot-wall MOCVD for Deep UV Applications. ECS Transactions, 2009, 25, 837-844.	0.5	1
101	In-grown stacking faults in 4H-SiC epilayers grown on off-cut substrates. Journal of Applied Physics, 2009, 105, .	2.5	27
102	Temperature Dependence and Selective Excitation of the Phosphorus Related Photoluminescence in 4H-SiC. Materials Science Forum, 2009, 615-617, 263-266.	0.3	0
103	Annealing effects on optical properties of low temperature grown ZnO nanorod arrays. Journal of Applied Physics, 2009, 105, .	2.5	123
104	Common point defects in as-grown ZnO substrates studied by optical detection of magnetic resonance. Journal of Crystal Growth, 2008, 310, 1006-1009.	1.5	4
105	Recombination centers in as-grown and electron-irradiated ZnO substrates. Journal of Applied Physics, 2007, 102, 093504.	2.5	18
106	Theory of the Stark Effect on the Donor Levels in 4H Silicon Carbide. Materials Science Forum, 2007, 556-557, 435-438.	0.3	1
107	Magnetic resonance studies of defects in electron-irradiated ZnO substrates. Physica B: Condensed Matter, 2007, 401-402, 507-510.	2.7	2
108	Uniform hot-wall MOCVD epitaxial growth of 2inch AlGaN/GaN HEMT structures. Journal of Crystal Growth, 2007, 300, 100-103.	1.5	30

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109	Extremely high quantum efficiency of donor-acceptor-pair emission in N-and-B-doped 6H-SiC. Journal of Applied Physics, 2006, 99, 093108.	2.5	67
110	Large-area free-standing GaN substrate grown by hydride vapor phase epitaxy on epitaxial lateral overgrown GaN template. Physica B: Condensed Matter, 2006, 371, 133-139.	2.7	15
111	Optical and morphological features of bulk and homoepitaxial ZnO. Superlattices and Microstructures, 2006, 39, 247-256.	3.1	10
112	Donor-Acceptor Pair Luminescence of Phosphorus-Aluminum and Nitrogen-Aluminum Pairs in 4H SiC. Materials Science Forum, 2006, 527-529, 601-604.	0.3	0
113	Effective-mass approximation for shallow donors in uniaxial indirect band-gap crystals and application to4Hâˆ’SiC. Physical Review B, 2006, 73, .	3.2	8
114	Highly homogeneous bulk-like 2â€²â€² GaN grown by HVPE on MOCVDâ€“GaN template. Journal of Crystal Growth, 2005, 275, e387-e393.	1.5	9
115	Influence of dislocation density on photoluminescence intensity of GaN. Journal of Crystal Growth, 2005, 278, 406-410.	1.5	5
116	Growth of thick GaN layers with hydride vapour phase epitaxy. Journal of Crystal Growth, 2005, 281, 17-31.	1.5	55
117	Hot-wall MOCVD grown homoepitaxial GaN layers with intense intrinsic excitonic structure. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 739-743.	1.8	2
118	High-Quality 2'' Bulk-Like Free-Standing GaN Grown by HydrideVapour Phase Epitaxy on a Si-doped Metal Organic Vapour Phase Epitaxial GaN Template with an Ultra Low Dislocation Density. Japanese Journal of Applied Physics, 2005, 44, 1181-1185.	1.5	45
119	Effective-Mass Theory of Shallow Donors in 4H-SiC. Materials Science Forum, 2005, 483-485, 511-514.	0.3	7
120	SiC and III-Nitride Growth in Hot-Wall CVD Reactor. Materials Science Forum, 2005, 483-485, 61-66.	0.3	8
121	Ionization energies of phosphorus and nitrogen donors and aluminum acceptors in4Hsilicon carbide from the donor-acceptor pair emission. Physical Review B, 2005, 71, .	3.2	48
122	Characterization of crack-free relaxed GaN grown on 2â€³ sapphire. Journal of Applied Physics, 2005, 98, 073525.	2.5	6
123	Characterization of High-Quality Free-Standing GaN Grown by HVPE. Physica Scripta, 2004, T114, 18-21.	2.5	4
124	Temperature-Dependent Hall Effect Measurements in Low â€“ Compensated p-Type 4H-SiC. Materials Science Forum, 2004, 457-460, 677-680.	0.3	11
125	Antisites as Possible Origin of Irradiation Induced Photoluminescence Centers in SiC: A Theoretical Study on Clusters of Antisites and Carbon Interstitials in 4H-SiC. Materials Science Forum, 2004, 457-460, 443-448.	0.3	1
126	Photoluminescence Excitation Spectroscopy on the Donor-Acceptor Pair Luminescence in 4H and 6H SiC. Materials Science Forum, 2004, 457-460, 585-588.	0.3	0

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127	Homoepitaxial On-Axis Growth of 4H- and 6H-SiC by CVD. Materials Science Forum, 2004, 457-460, 193-196.	0.3	15
128	Hydride vapor-phase epitaxial GaN thick films for quasi-substrate applications: Strain distribution and wafer bending. Journal of Electronic Materials, 2004, 33, 389-394.	2.2	20
129	Micro-Raman scattering profiling studies on HVPE-grown free-standing GaN. Physica Status Solidi A, 2004, 201, 2773-2776.	1.7	12
130	Direct experimental evidence for unusual effects of hydrogen on the electronic and vibrational properties ofGaNxP1âˆ’xalloys: A proof for a general property of dilute nitrides. Physical Review B, 2004, 70, .	3.2	24
131	Defects in SiC. Physica B: Condensed Matter, 2003, 340-342, 15-24.	2.7	22
132	Anti-site pair in SiC: a model of the DI center. Physica B: Condensed Matter, 2003, 340-342, 175-179.	2.7	7
133	Fast growth of high quality GaN. Physica Status Solidi A, 2003, 200, 13-17.	1.7	42
134	Photoluminescence Up-Conversion Processes in SiC. Materials Science Forum, 2003, 433-436, 309-312.	0.3	0
135	Correlation between the antisite pair and theDIcenter in SiC. Physical Review B, 2003, 67, .	3.2	72
136	Donor-Acceptor Pair Luminescence in 4H-SiC Doped with Nitrogen and Aluminum. Materials Science Forum, 2003, 433-436, 321-324.	0.3	1
137	Analysis of the sharp donor-acceptor pair luminescence in4H-SiC doped with nitrogen and aluminum. Physical Review B, 2003, 67, .	3.2	31
138	Optical selection rules for shallow donors in4Hâˆ’SiCand ionization energy of the nitrogen donor at the hexagonal site. Physical Review B, 2003, 67, .	3.2	17
139	Excitation spectra of nitrogen bound excitons in 4H- and 6H-SiC. Journal of Applied Physics, 2002, 91, 2028-2032.	2.5	6
140	Photoconductivity of Lightly-Doped and Semi-Insulating 4H-SiC and the Free Exciton Binding Energy. Materials Science Forum, 2002, 389-393, 613-616.	0.3	6
141	Photoluminescence upconversion in 4Hâ€“SiC. Applied Physics Letters, 2002, 81, 2547-2549.	3.3	3
142	Tunable laser spectroscopy of spin injection in ZnMnSe/ZnCdSe quantum structures. Applied Physics Letters, 2002, 81, 2196-2198.	3.3	29
143	Resonant sharp hot free-exciton luminescence in 6H- and 4H-SiC due to inhibited exciton-phonon interaction. Physical Review B, 2001, 64, .	3.2	11
144	Spin Polarization and Injection in ZnMnSe/ZnCdSe Heterostructures. Materials Research Society Symposia Proceedings, 2001, 690, F1.7.1.	0.1	0

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145	Photoluminescence line-shape analysis in quantum wells embedded in superlattices. Materials Science and Engineering C, 2001, 15, 75-77.	7.3	3
146	Intrinsic Photoconductivity of 6H-SiC and the Free-Exciton Binding Energy. Materials Science Forum, 2001, 353-356, 405-408.	0.3	2
147	Photoluminescence study of AlAs/GaAs superlattices containing enlarged wells. Thin Solid Films, 2000, 364, 224-227.	1.8	6
148	High-temperature excitons in GaAs quantum wells embedded in AlAs/GaAs superlattices. Vacuum, 2000, 58, 478-484.	3.5	7
149	Effect of non-abrupt interfaces in AlAs/GaAs superlattices with embedded GaAs quantum wells. Vacuum, 2000, 58, 561-567.	3.5	3
150	Vibrational properties and structure of undoped and Al-doped ZnO films deposited by RF magnetron sputtering. Thin Solid Films, 2000, 379, 28-36.	1.8	228
151	Excitation properties of hydrogen-related photoluminescence in6Hâˆ’SiC. Physical Review B, 2000, 62, 7162-7168.	3.2	10
152	Pseudo-Donors in SiC. Materials Science Forum, 2000, 338-342, 647-650.	0.3	5
153	Metastability of a Hydrogen-related Defect in 6H-SiC. Materials Science Forum, 2000, 338-342, 651-654.	0.3	9
154	B implantation in 6Hâ€“SiC: Lattice damage recovery and implant activation upon high-temperature annealing. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1040.	1.6	6
155	Thick GaN Layers Grown on A-plane Sapphire Substrates by Hydride Vapour Phase Epitaxy. Physica Scripta, 1999, T79, 67.	2.5	10
156	Contribution of free-electron recombination to the luminescence spectra of thick GaN films grown by hydride vapor phase epitaxy. Journal of Applied Physics, 1999, 85, 7888-7892.	2.5	34
157	Zeeman spectroscopy of the D1 bound exciton in 3Câ€“, and 4Hâ€“SiC. Physica B: Condensed Matter, 1999, 273-274, 677-680.	2.7	8
158	Vibrational studies of copper thiogallate solid solutions. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 57, 102-109.	3.5	32
159	Photoluminescence of 4H-SiC: some remarks. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 61-62, 234-238.	3.5	6
160	Photoluminescence excitation spectra of the free exciton emission in 6Hâ€“SiC. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 61-62, 265-269.	3.5	4
161	Liquid phase epitaxial growth of SiC. Journal of Crystal Growth, 1999, 197, 147-154.	1.5	65
162	Photoluminescence of electron-irradiated4Hâˆ’SiC. Physical Review B, 1999, 59, 8008-8014.	3.2	64

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163	Properties of theD1bound exciton in4Hâˆ’SiC. Physical Review B, 1999, 59, 1956-1963.	3.2	80
164	Excitation Properties of SiC Photoluminescence. Physica Scripta, 1999, T79, 50.	2.5	1
165	The material quality of CVD-grown SiC using different carbon precursors. Journal of Crystal Growth, 1998, 183, 163-174.	1.5	31
166	The D1 Exciton in 4H-SiC. Physica Status Solidi (B): Basic Research, 1998, 210, 337-340.	1.5	5
167	Properties of molecular-beam epitaxy-grown GaNAs from optical spectroscopy. Journal of Applied Physics, 1998, 84, 3830-3835.	2.5	83
168	6H-SiC Crystallinity Behaviour upon B Implantation Studied by Raman Scattering. Materials Science Forum, 1998, 264-268, 741-744.	0.3	0
169	High Growth Rate of Î±-SiC by Sublimation Epitaxy. Materials Science Forum, 1998, 264-268, 143-146.	0.3	15
170	Near Band-Gap Emission in V-Implanted and Annealed 4H-SiC. Materials Science Forum, 1998, 264-268, 497-500.	0.3	2
171	Cathodoluminescence of Defect Regions in SiC Epi-Films. Materials Science Forum, 1998, 264-268, 653-656.	0.3	6
172	CVD Growth and Characterisation of SiC Epitaxial Layers on Faces Perpendicular to the (0001) Basal Plane. Materials Science Forum, 1998, 264-268, 123-126.	0.3	17
173	Changes in the Exciton-Related Photoluminescence of 4H- and 6H-SiC Induced by Uniaxial Stress. Materials Science Forum, 1998, 264-268, 489-492.	0.3	5
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